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AF/2824
#8/A (AL)
PATENT 8-21-02
Molise

Docket No.: 49657-862

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

: **RESPONSE UNDER 37 CFR 1.116**

Naoki TSUJI

: **EXPEDITED PROCEDURE**

Serial No.: 09/745,468

: Group Art Unit: 2824

Filed: December 26, 2000

: Examiner: B. Owens

For: SEMICONDUCTOR DEVICE AND A PRODUCTION METHOD FOR THE SAME

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MAY 15 2002
TC 2800 MAIL ROOM

AMENDMENT UNDER 37 CFR §1.116

Box AF
Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated February 13, 2002, pursuant to the provisions of 37 C.F.R. §1.116.

IN THE CLAIMS:

Please amend claims 1 and 2 as follows.

1. (Amended) A semiconductor device comprising:

a first region where first transistors each having a first gate oxide film of a first thickness is formed;

a second region, adjacent to the first region, where second transistors each having a second gate oxide film of a second thickness are formed;

trench isolation [regions] patterns formed selectively within said first and second regions and extending continuously in a first direction; and